TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7SA04F,TC7SA04FU

Inverter with 3.6 V Tolerant Input and Output

Features

- Low voltage operation : $V_{CC} = 1.8 \sim 3.6 V$
- High speed operation $: t_{pd} = 2.8 \text{ ns} (\text{max}) (V_{CC} = 3.0 \sim 3.6 \text{ V})$
 - $t_{pd} = 3.7 \text{ ns} (\text{max}) (\text{V}_{CC} = 2.3 \sim 2.7 \text{ V})$
 - $: t_{pd} = 7.4 \text{ ns} (max) (V_{CC} = 1.8 \text{ V})$
- High Output current $: I_{OH}/I_{OL} = \pm 24 \text{ mA (min)} (V_{CC} = 3.0 \text{ V})$ $: I_{OH}/I_{OL} = \pm 18 \text{ mA (min)} (V_{CC} = 2.3 \text{ V})$
 - $IOH/IOL = \pm 6 \text{ mA (min) (VCC = 2.3 V)}$ $IOH/IOL = \pm 6 \text{ mA (min) (VCC = 1.8 V)}$
- Latch-up performance : ±300 mA or more
- ESD performance : Human body model > ±200 V : Machine model > ±200 V
- Power down protection is provided on all inputs and outputs.
- TC74VCX04FT equivalent.



Weight SSOP5-P-0.95 : 0.016 g (typ.) SSOP5-P-0.65A : 0.006 g (typ.)

Characteristics	Symbol	Rating	Unit	
Power supply voltage	V _{CC}	-0.5~4.6	V	
DC input voltage	V _{IN}	-0.5~4.6	V	
DC output voltage	Vout	-0.5~4.6 (Note 1)	V	
DC output voitage	VOUT	-0.5~V _{CC} + 0.5 (Note 2)	v	
Input diode current	I _{IK}	-50	mA	
Output diode current	I _{OK}	±50 (Note 3)	mA	
DC output current	I _{OUT}	±50	mA	
Power dissipation	PD	200	mW	
DC V _{CC} /ground current	ICC	±100	mA	
Storage temperature range	T _{stg}	-65~150	°C	

Maximum Ratings (Ta = 25°C)

Note 1: $V_{CC} = 0 V$

Note 2: High or low state. IOUT absolute maximum rating be observed.

Note 3: V_{OUT} < GND, V_{OUT} > V_{CC}

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Marking



Pin Assignment (top view)



Logic Diagram



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А	Y
L	Н
Н	L

Recommended Operating Range

Characteristics	Symbol	Rating	Unit
Dewer eventy veltage	Mar	1.8~3.6	V
Power supply voltage	V _{CC}	1.2~3.6 (Note 4)	v
Input voltage	V _{IN}	-0.3~3.6	V
Output voltage	V _{OUT}	0~3.6 (Note 5)	V
Oulput voltage		0~V _{CC} (Note 6)	v
		±24 (Note 7)	
Output current	I _{OH} /I _{OL}	±18 (Note 8)	mA
		±6 (Note 9)	
Operating temperature range	T _{opr}	-40~85	°C
Input rise and fall time	dt/dv	0~10 (Note 10)	ns/V

Note 4: Data retention only

Note 5: $V_{CC} = 0 V$

Note 6: High or low state

Note 7: V_{CC} = 3.0~3.6 V

Note 8: $V_{CC} = 2.3 \sim 2.7 \text{ V}$

Note 9: $V_{CC} = 1.8 V$

Note 10: $V_{IN} = 0.8 \sim 2.0 \text{ V}, \text{ V}_{CC} = 3.0 \text{ V}$

Electrical Characteristics

DC Characteristics (Ta = –40~85°C, 2.7 V < V_{CC} \leq 3.6 V)

Characteristics		Symbol	Tos	Test Condition		Min	Мах	Unit
Charac	clensues	Symbol	Test Condition		V _{CC} (V)	IVIIII	IVIAX	Onic
Input voltage	High level	V _{IH}		_	2.7~3.6	2.0	_	V
Input voltage	Low level	V _{IL}			2.7~3.6	_	0.8	v
			I _{OH} = −100 μA	2.7~3.6	V _{CC} - 0.2	_		
	High level	V _{OH}	$V_{IN} = V_{IL}$	I _{OH} = -12 mA	2.7	2.2	_	V
Output voltage				I _{OH} = -18 mA	3.0	2.4	_	
				I _{OH} = -24 mA	3.0	2.2	_	
		V _{OL}	V _{OL} V _{IN} = V _{IH}	I _{OL} = 100 μA	2.7~3.6		0.2	
				I _{OL} = 12 mA	2.7	_	0.4	
	Low level			I _{OL} = 18 mA	3.0	_	0.4	
				I _{OL} = 24 mA	3.0	_	0.55	
Input leakage curre	ent	I _{IN}	I _{IN} V _{IN} = 0~3.6 V		2.7~3.6		±5.0	μA
Power off leakage	current	I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μA
		laa	$V_{IN} = V_{CC}$ or C	$V_{IN} = V_{CC}$ or GND			20.0	
Quiescent supply of	Surrent	Icc	$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.6 \text{ V}$		2.7~3.6		±20.0	μ A
Increase in I _{CC} pe	r input	Δlcc	$V_{IH} = V_{CC} - 0.$	6 V	2.7~3.6	_	750	

DC Characteristics (Ta = $-40 \sim 85^{\circ}$ C, 2.3 V \leq V_{CC} \leq 2.7 V)

Characteristics		Symbol	Symbol Test Condition			Min	Max	Unit
		Symbol	Te	st Condition	V _{CC} (V)	IVIIII	wax	Unit
Input voltage	High level	V _{IH}		_	2.3~2.7	1.6		v
input voltage	Low level	VIL			2.3~2.7	_	0.7	v
			I _{OH} = -100 μA	2.3~2.7	V _{CC} - 0.2	_		
	High level	V _{OH}	$V_{IN} = V_{IL}$	I _{OH} = -6 mA	2.3	2.0		- v
	_			I _{OH} = -12 mA	2.3	1.8		
Output voltage				I _{OH} = -18 mA	2.3	1.7		
			$V_{IN} = V_{IH}$	I _{OL} = 100 μA	2.3~2.7	_	0.2	
	Low level	V _{OL}		$I_{OL} = 12 \text{ mA}$	2.3	_	0.4	
				I _{OL} = 18 mA	2.3		0.6	
Input leakage curr	ent	I _{IN}	V _{IN} = 0~3.6 V		2.3~2.7		±5.0	μA
Power off leakage	current	I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0		10.0	μA
Quiescent supply current			$V_{IN} = V_{CC}$ or ($V_{IN} = V_{CC}$ or GND		_	20.0	
		Icc	$V_{CC} \leq (V_{IN}, V_{IN})$	$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.6 \text{ V}$			±20.0	μA

DC Characteristics (Ta = -40~85°C, 1.8 V \leq V_{CC} < 2.3 V)

Charao	teristics	Symbol	Test Condition			Min	Max	Unit
					V _{CC} (V)			
Input voltage	High level	V _{IH}			1.8~2.3	$0.7 \times V_{CC}$		v
input voltage	Low level	V _{IL}			1.8~2.3		$0.2 \times V_{CC}$	v
	High level V _{OH}		VIN = VII	I _{OH} = -100 μA	1.8	V _{CC} - 0.2	_	
Output voltage	-			I _{OH} =6 mA	1.8	1.4	_	V
		M	$V_{IN} = V_{IH}$	I _{OL} = 100 μA	1.8	_	0.2	
	Low level	V _{OL}		I _{OL} = 6 mA	1.8	_	0.3	
Input leakage curre	ent	l _{IN}	V _{IN} = 0~3.6 V		1.8		±5.0	μA
Power off leakage	current	I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μA
Quiescent supply current			$V_{IN} = V_{CC}$ or GND		1.8		20.0	μA
Quescent supply (Juneni	Icc	$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.6 \text{ V}$		1.8		±20.0	μΑ

AC Characteristics (Ta = -40~85°C, input: $t_r = t_f = 2.0 \text{ ns}$, $C_L = 30 \text{ pF}$, $R_L = 500 \Omega$)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Min	Max	Unit
Propagation delay time		Figure 1, Figure 2	1.8	1.0	7.4	
			2.5 ± 0.2	0.8	3.7	ns
	t _{pHL}		$\textbf{3.3}\pm\textbf{0.3}$	0.6	2.8	

For $C_L = 50 \text{ pF}$, add approximately 300 ps to the AC maximum specification.

Dynamic Switching Characteristics (Ta = 25° C, input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF)

Characteristics	Symbol	Test Condition		_	Turp	Unit
Characteristics	Symbol	Test Condition		$V_{CC}(V)$	Тур.	Unit
		$V_{IN} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$	(Note 11)	1.8	0.25	
Quiet output maximum dynamic V_{OL}	V _{OLP}	$V_{IN} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$	(Note 11)	2.5	0.6	ns
		$V_{IN} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$	(Note 11)	3.3	0.8	
	V _{OLV}	$V_{IN} = 1.8 V, V_{IL} = 0 V$	(Note 11)	1.8	-0.25	
Quiet output minimum dynamic V_{OL}		$V_{IN} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$	(Note 11)	2.5	-0.6	ns
		$V_{IN} = 3.3 \text{ V}, \text{ V}_{IL} = 0 \text{ V}$	(Note 11)	3.3	-0.8	
		$V_{IN} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$	(Note 11)	1.8	1.5	
Quiet output minimum dynamic V_{OH}	V _{OLP}	V _{IN} = 2.5 V, V _{IL} = 0 V	(Note 11)	2.5	1.9	ns
		$V_{IN} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$	(Note 11)	3.3	2.2	

Note 11: Parameter guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

Characteristics	Symbol	Symbol Test Condition			Тур.	Unit
Characteristics	Symbol	Test Condition	V _{CC} (V)	тур.	Unit	
Input capacitance	C _{IN}	—		1.8, 2.5, 3.3	5	pF
Power dissipation capacitance	C _{PD}	f _{IN} = 10 MHz	(Note 12)	1.8, 2.5, 3.3	18	рF

Note 12: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation.

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

AC Test Circuit





AC Wareform



Symbol	V _{CC}						
Symbol	$3.3 \pm 0.3 \ V \qquad 2.5 \pm 0.2 \ V$		1.8 V				
VIH	2.7 V	V _{CC}	V _{CC}				
VM	1.5 V	V _{CC} /2	V _{CC} /2				



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Package Dimensions

SSOP5-P-0.95

Unit : mm





Weight: 0.016 g (typ.)

TOSHIBA

Package Dimensions

Unit : mm





Weight: 0.006 g (typ.)

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